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Vishay Semiconductors

# Thyristor High Voltage, Phase Control SCR, 40 A



PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub> 35 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V			
V <sub>TM</sub>	1.45 V			
I <sub>GT</sub>	150 mA			
$T_J$	-40 °C to +125 °C			
Package	TO-247AC 3L			
Circuit configuration	Single SCR			

#### **FEATURES**

- Designed and qualified according to JEDEC®-JESD 47
- Low IGT parts available
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



#### **APPLICATIONS**

 Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding and battery charge

#### **DESCRIPTION**

The VS-40TPS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I <sub>T(AV)</sub>	Sinusoidal waveform	35	Δ.			
I <sub>RMS</sub>		55	A A			
V <sub>RRM</sub> /V <sub>DRM</sub>		800 to 1200	V			
I <sub>TSM</sub>		600	A			
V <sub>T</sub>	40 A, T <sub>J</sub> = 25 °C	1.45	V			
dV/dt		1000	V/µs			
dl/dt		100	A/µs			
T <sub>J</sub>		-40 to +125	°C			

VOLTAGE RATINGS						
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA			
VS-40TPS08A-M3	800	900				
VS-40TPS08-M3	800	900	10			
VS-40TPS12A-M3	1200	1300	10			
VS-40TPS12-M3	1200	1300				



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<b>ABSOLUTE MAXIMUM RATINGS</b>					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 79 °C, 180° conduction half sine wav	е	35	
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>			55	Α
Maximum peak, one-cycle	L	10 ms sine pulse, rated V <sub>RRM</sub> applied		500	
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no voltage reapplied		600	
Maximum I <sup>2</sup> t for fusing	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied	Initial $T_{.1} = T_{.1} max$ .	1250	A <sup>2</sup> s
Maximum 1-t for fusing	1-1	10 ms sine pulse, no voltage reapplied	ij – ijiilax.	1760	A-5
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 ms to 10 ms, no voltage reapplied		17 600	A <sup>2</sup> √s
Low level value of threshold voltage	V <sub>T(TO)1</sub>		1.02	V	
High level value of threshold voltage	V <sub>T(TO)2</sub>	T <sub>J</sub> = 125 °C			V
Low level value of on-state slope resistance	r <sub>t1</sub>				0
High level value of on-state slope resistance	r <sub>t2</sub>			7.50	mΩ
Maximum peak on-state voltage	$V_{TM}$	110 A, T <sub>J</sub> = 25 °C		1.85	V
Maximum rate of rise of turned-on current	dl/dt	T <sub>J</sub> = 25 °C		100	A/µs
Maximum holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial T	= 1 A, I <sub>T</sub> = 25 °C	200	
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C		300	
		$T_{J} = 25  ^{\circ}\text{C}$ $T_{J} = 125  ^{\circ}\text{C}$ $V_{R} = \text{Rated V}_{RRM}/V_{DRM}$		0.5	mA
Maximum reverse and direct leakage current	I <sub>RRM/</sub> I <sub>DRM</sub>			10	
Maximum rate of rise of off-state voltage 40TPS12A	a) (/d+	$T_J = T_J$ maximum, linear to 80 % $V_{DRM}$ , $R_g$ - $k$ = 100 $\Omega$		500	\//··-
Maximum rate of rise of off-state voltage 40TPS12	dV/dt			1000	V/µs

TRIGGERING						
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS	
Maximum peak gate power	P <sub>GM</sub>			10	W	
Maximum average gate power	P <sub>G(AV)</sub>			2.5	VV	
Maximum peak gate current	I <sub>GM</sub>			2.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>			10	V	
		T <sub>J</sub> = - 40 °C		4.0	V	
Maximum required DC gate voltage to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	2.5		
		T <sub>J</sub> = 125 °C	100iolivo ioaa	1.7		
	I <sub>GT</sub>	T <sub>J</sub> = - 40 °C	Anode supply = 6 V resistive load	270	mA	
Maximum vaguired DC acts aurent to triager		T <sub>J</sub> = 25 °C		150		
Maximum required DC gate current to trigger		T <sub>J</sub> = 125 °C		80		
		$T_J$ = 25 °C, for 40TPSAPbF and 40TPSA-M3		40		
Maximum DC gate voltage not to trigger for 40TPS12	$V_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value		0.25	V	
Maximum DC gate current not to trigger for 40TPS12	I <sub>GD</sub>			6	mA	
Maximum DC gate voltage not to trigger for 40TPS12A	$V_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value		0.15	V	
Maximum DC gate current not to trigger for 40TPS12A	I <sub>GD</sub>			1	mA	



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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	SOL TEST CONDITIONS		UNITS	
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C	
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation	0.6		
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>	DC operation		°C/W	
Maximum thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.2		
Approximate weight				6	g	
Approximate weight				0.21	oz.	
Mounting torque	minimum			6 (5)	kgf · cm	
Mounting torque — maximum				12 (10)	(lbf·in)	
Marking device				40TPS08A		
			Coop at de TO 247AC 21	40TPS12A		
			Case style TO-247AC 3L	40TPS08		
				40TPS12		

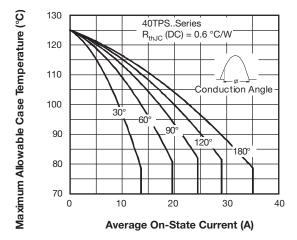


Fig. 1 - Current Rating Characteristics

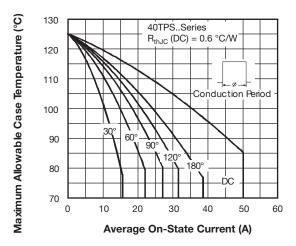


Fig. 2 - Current Rating Characteristics

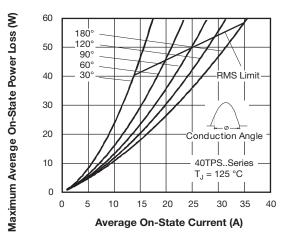


Fig. 3 - On-State Power Loss Characteristics

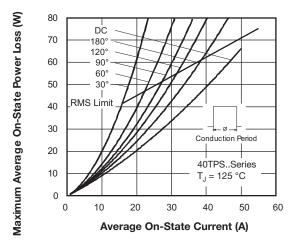


Fig. 4 - On-State Power Loss Characteristics



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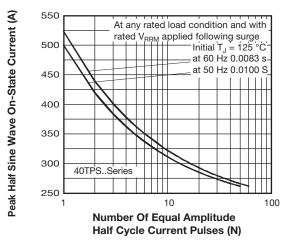


Fig. 5 - Maximum Non-Repetitive Surge Current

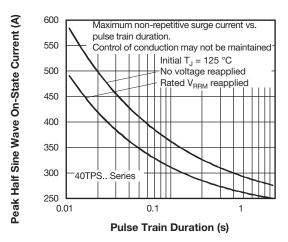


Fig. 6 - Maximum Non-Repetitive Surge Current

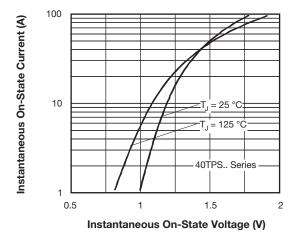


Fig. 7 - On-State Voltage Drop Characteristics



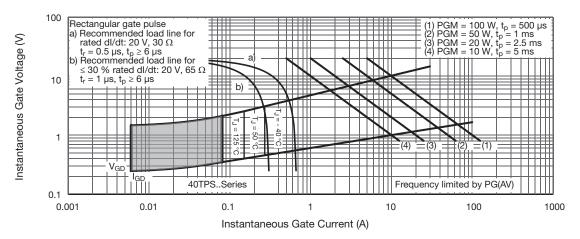


Fig. 8 - Gate Characteristics

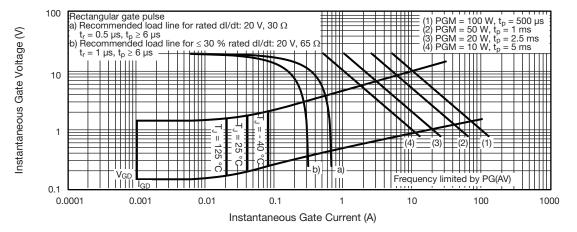


Fig. 9 - Gate Characteristics, 40TPS..A Series

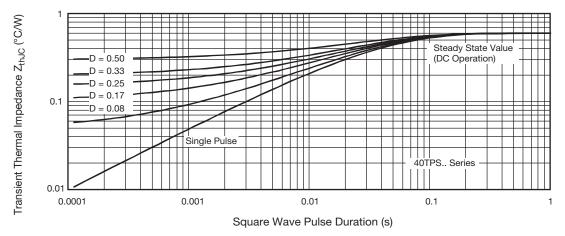


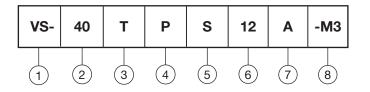
Fig. 10 - Thermal Impedance ZthJC Characteristics



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### **ORDERING INFORMATION TABLE**

Device code



- Vishay Semiconductors product

**2** - Current rating (40 = 40 A)

**3** - Circuit configuration:

T = thyristor

4 - Package:

P = TO-247AC 3L

5 - Type of silicon:

S = standard recovery rectifier

08 = 800 V12 = 1200 V

Voltage ratings

• A = low I<sub>GT</sub> selection 40 mA maximum

• None = standard lgt selection

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-40TPS08A-M3	25	500	Antistatic plastic tubes			
VS-40TPS08-M3	25	500	Antistatic plastic tubes			
VS-40TPS12A-M3	25	500	Antistatic plastic tubes			
VS-40TPS12-M3	25	500	Antistatic plastic tubes			

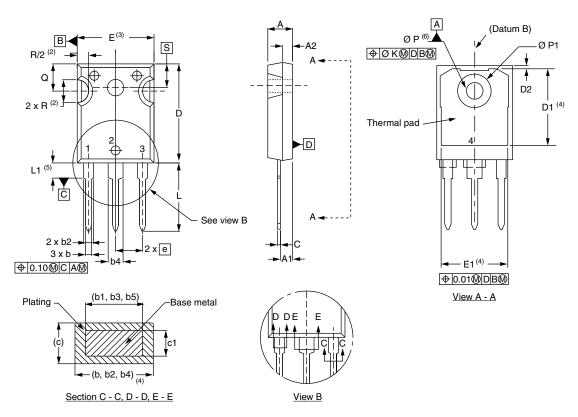
LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?96138</u>				
Part marking information	www.vishay.com/doc?95007			



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### **TO-247AC 3L**

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIN	MILLIMETERS		HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.17	1.37	0.046	0.054	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.35	0.020	0.053	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46	BSC	0.215	BSC	
ØK	0.254		0.0	)10	
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	7.39	-	0.291	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217	BSC	
	·		·	·	·

#### **Notes**

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension Q



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